

Customer No.: 91343

Application No.: 10/605,304

Docket NO.: 11080-US-PA

**In The Specification:**

Please amend paragraph [0010] as follows:

[0010] Referring to Figure 1D, the conformal doped layer 108, not covered by the photoresist layer is removed, leaving the doped layer ~~10a8~~ 108a at the bottom of the deep trench 102a. The photoresist layer 110 is subsequently removed. A thermal process is further conducted to drive in the dopants in the doped layer 108a into the substrate 100 to form a doped region 112, wherein the doped region 112 serves as the buried plate of the deep trench capacitor. Thereafter, the doped layer 108a in the deep trench 102a is removed as shown in Figure 1E to complete the fabrication of a buried plate of a deep trench capacitor.